

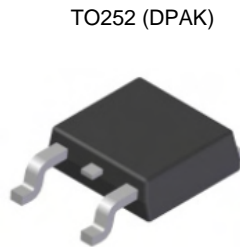
Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C (Note 6)
-40V	25mΩ @ V _{GS} = -10V	-40A
	45mΩ @ V _{GS} = -4.5V	-33A

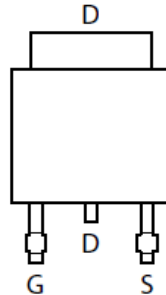
Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

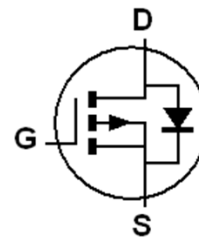
- Motor controls
- Backlighting
- DC-DC converters
- Printer equipment



Top View



Top View
Pin Out



Device Symbol

Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Low Input/Output Leakage
- 100% Unclamped Inductive Switch (UIS) Test in Production
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.**
<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

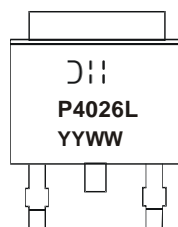
- Package: TO252
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.315 grams (Approximate)

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP4026LK3-13	TO252 (DPAK)	2,500	Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



- Diodes logo = Manufacturer's Marking
- P4026L = Product Type Marking Code
- YYWW = Date Code Marking
- YY = Year (ex: 23 = 2023)
- WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-40	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _C = +25°C	I _D	-40	A
		T _C = +70°C		-32	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-160	A
Maximum Body Diode Forward Current (Note 6)			I _S	-40	A
Avalanche Current, L = 0.3mH			I _{AS}	-22.9	A
Avalanche Energy, L = 0.3mH			E _{AS}	78.7	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	3.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	35	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	P _D	70	W
Thermal Resistance, Junction to Case (Note 6)	Steady State	R _{θJC}	1.77	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-40	—	—	V	I _D = -250µA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _{DS} = -40V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.8	—	-1.8	V	I _D = -250µA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance	R _{DS(ON)}	—	13	25	mΩ	V _{GS} = -10V, I _D = -3A
			17	45		V _{GS} = -4.5V, I _D = -3A
Diode Forward Voltage	V _{SD}	—	-0.7	-1	V	I _S = -1A, V _{GS} = 0V
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	2064	—	pF	V _{DS} = -20V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	212	—		
Reverse Transfer Capacitance	C _{rss}	—	183	—		
Gate Resistance	R _g	—	2.5	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -10V)	Q _g	—	45.8	—	nC	V _{DS} = -20V, I _D = -3A
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	23.5	—		
Gate-Source Charge	Q _{gs}	—	5	—		
Gate-Drain Charge	Q _{gd}	—	6.7	—		
Turn-On Delay Time	t _{d(ON)}	—	4.3	—	ns	V _{GS} = -10V, V _{DD} = -20V, I _D = -3A, R _g = 6Ω
Turn-On Rise Time	t _r	—	4.7	—		
Turn-Off Delay Time	t _{d(OFF)}	—	71.8	—		
Turn-Off Fall Time	t _f	—	23.9	—		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

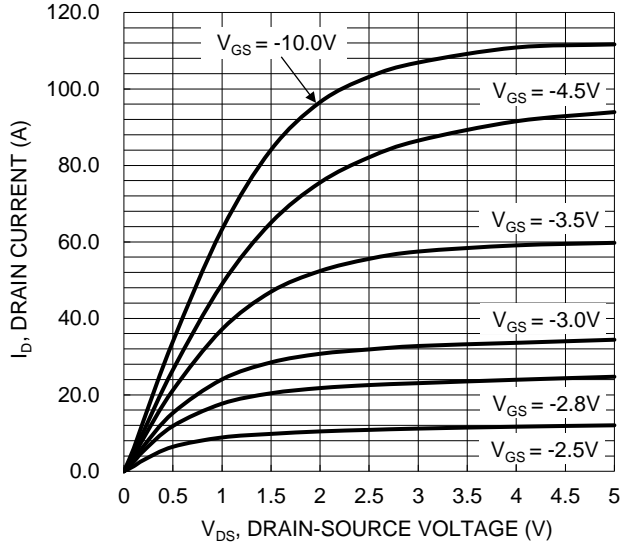


Figure 1. Typical Output Characteristic

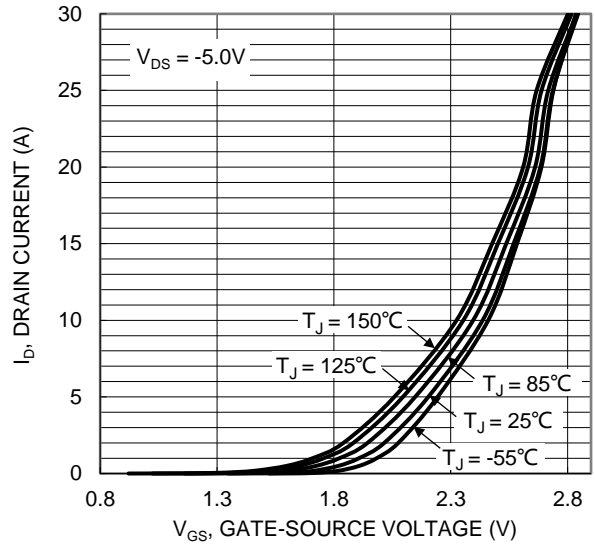


Figure 2. Typical Transfer Characteristic

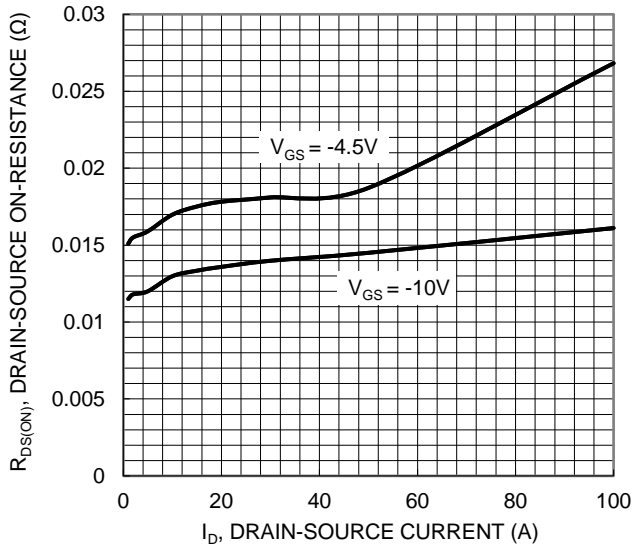


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

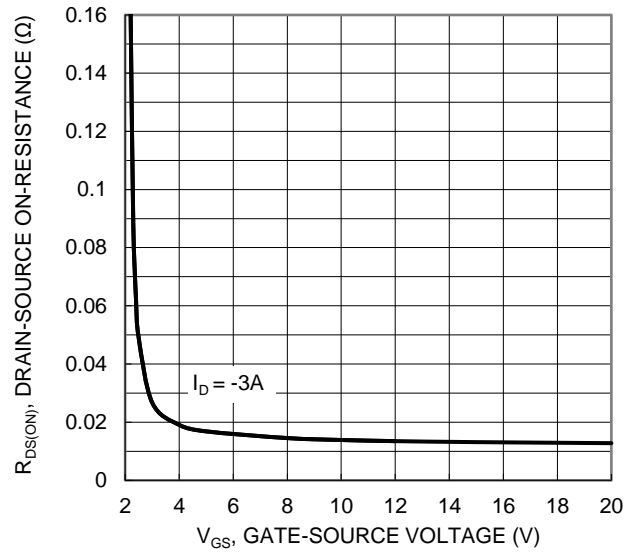


Figure 4. Typical Transfer Characteristic

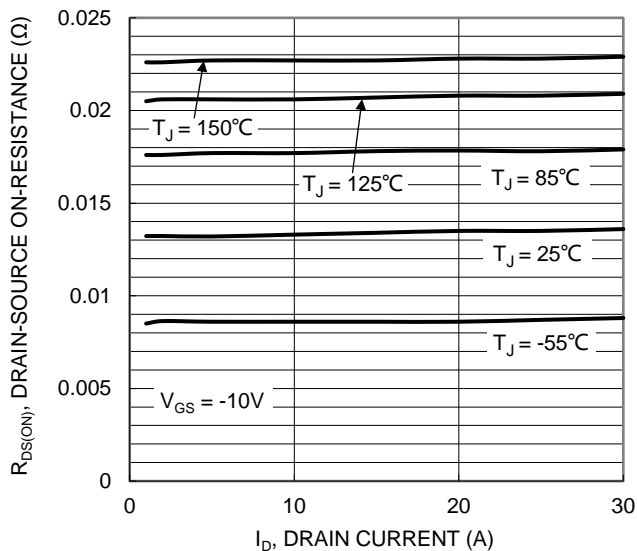


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

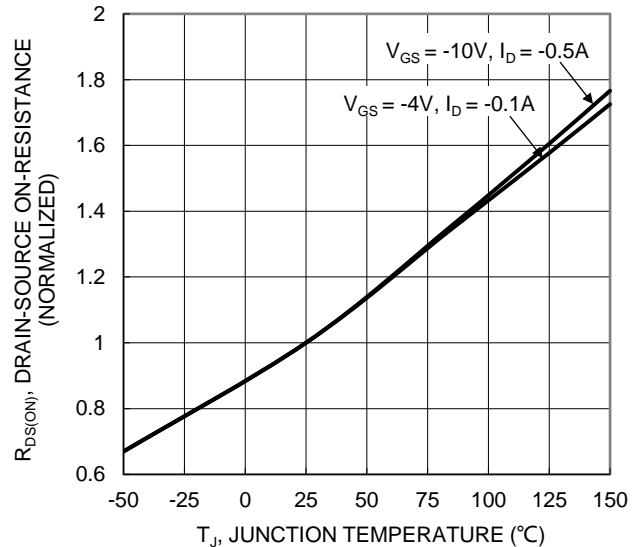


Figure 6. On-Resistance Variation with Junction Temperature

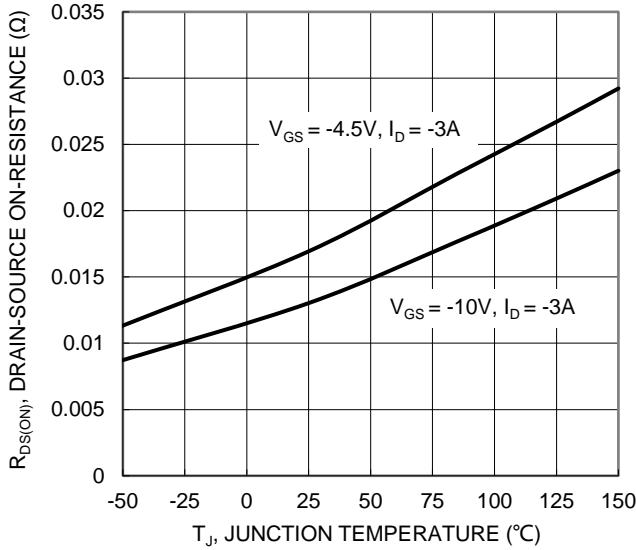


Figure 7. On-Resistance Variation with Junction Temperature

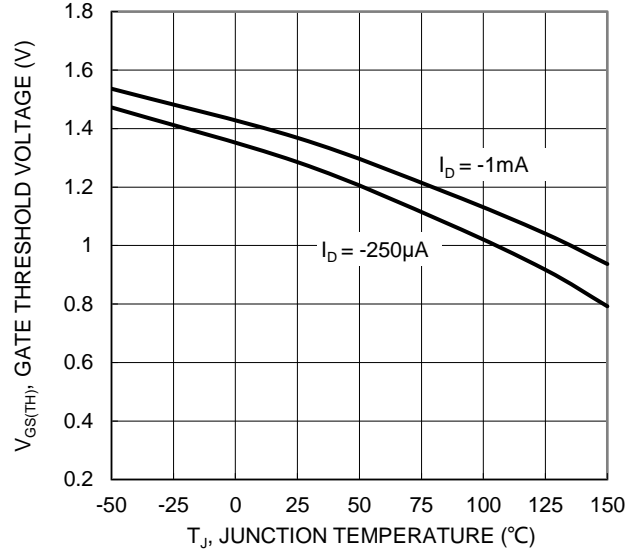


Figure 8. Gate Threshold Variation vs. Junction Temperature

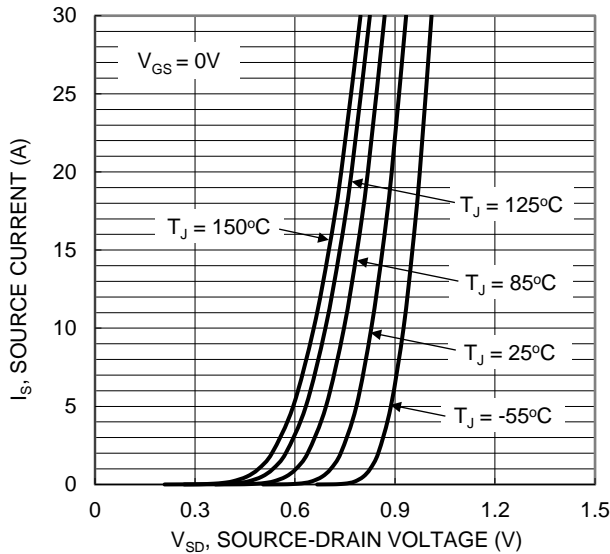


Figure 9. Diode Forward Voltage vs. Current

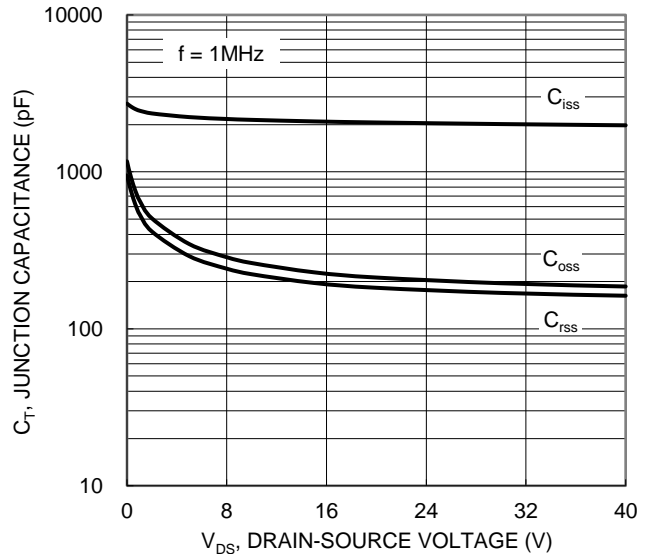


Figure 10. Typical Junction Capacitance

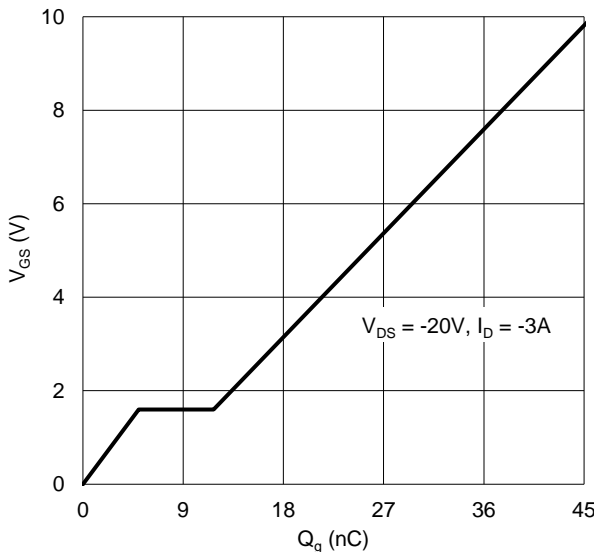


Figure 11. Gate Charge

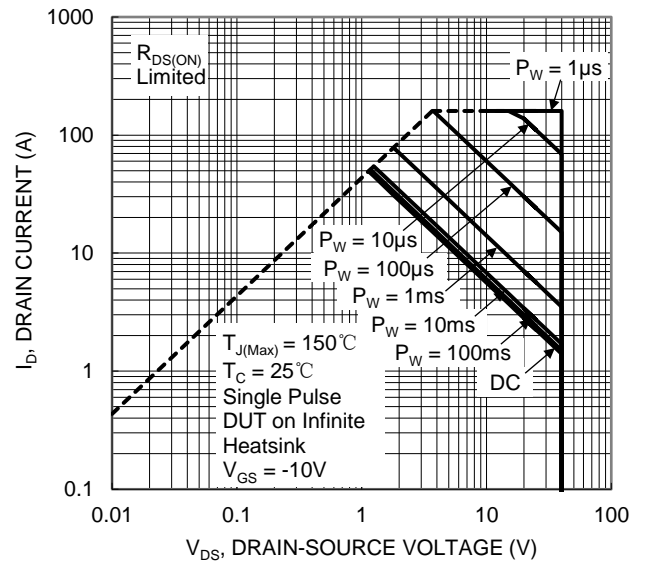


Figure 12. SOA, Safe Operation Area

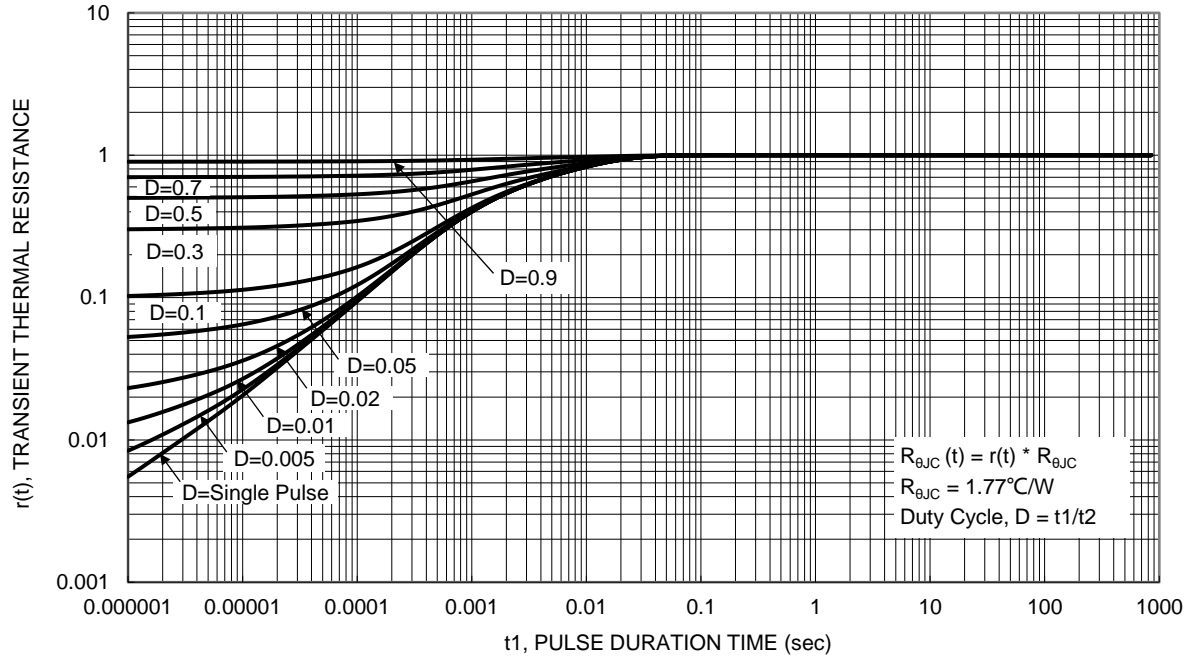
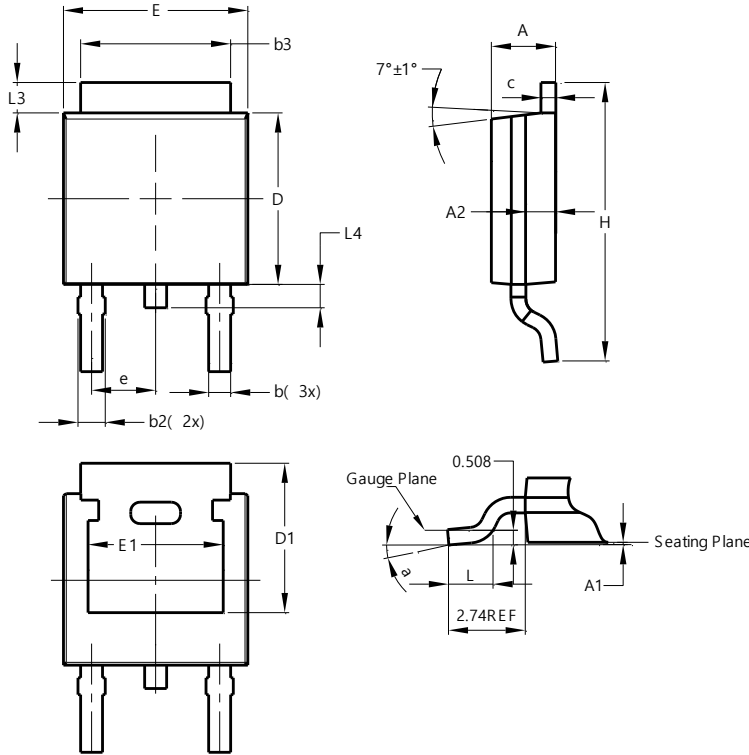


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

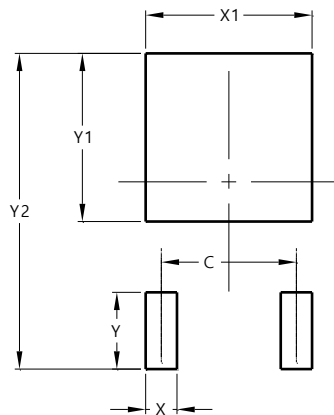


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.50	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	--	--
e	2.286 BSC		
E	6.45	6.70	6.58
E1	4.32	--	--
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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